



#5/PREZ  
A702  
10/20/99

PATENT

ATTORNEY DOCKET NO. 07977/093002/US3164D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ohtani, et al.

Art Unit: 2812

Serial No.: 09/379,702

Examiner:

Filed : August 24, 1999

Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Assistant Commissioner for Patents  
Washington, DC 20231

PRELIMINARY AMENDMENT

Sir:

Prior to initial examination, kindly amend the above-identified application as follows:

In the Claims:

Please cancel claim 1 without prejudice.

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OCT 07 1999

TECHNOLOGY CENTER 2800

Please add the following new claims.

2. A semiconductor device comprising:  
a crystalline semiconductor layer comprising silicon over  
a substrate; and

an insulating layer comprising a thermal oxide of said  
semiconductor layer, said thermal oxide being provided in contact  
with a surface of said semiconductor layer and constituting a part  
of a gate insulating layer of said semiconductor device,

10/05/1999 ZABDALLA 00000044 09379702

01 FC:103  
02 FC:102

414.00 OP  
546.00 OP

Date of Deposit 9-27-99  
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Jane Christy  
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